

<b>SANYO</b>	No.4540	<b>3SK248</b>
		N-Channel Enhancement MOS Silicon FET Muting/Switching Applications

**Features**

- MOS FET with a back gate terminal.
- Enhancement type.
- Small ON resistance.
- Small-sized package permitting 3SK248-applied sets to be made smaller and slimmer.

**Absolute Maximum Ratings at Ta = 25°C**

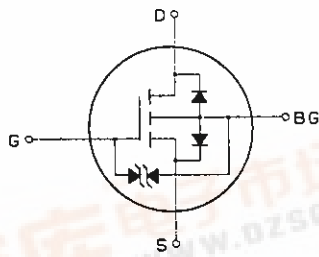
			unit
Drain-to-Source Voltage	V <sub>DSS</sub>	10	V
Gate-to-Source Voltage	V <sub>GSS</sub>	±10	V
Drain Current	I <sub>D</sub>	100	mA
Allowable Power Dissipation	P <sub>D</sub>	200	mW
Channel Temperature	T <sub>ch</sub>	125	°C
Storage Temperature	T <sub>stg</sub>	-55 to +125	°C

**Electrical Characteristics at Ta = 25°C**

			min	typ	max	unit
D-S Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 μA, V <sub>GS</sub> = 0V	10			V
G-S Breakdown Voltage	V <sub>GSS</sub>	I <sub>G</sub> = ±10 μA, V <sub>DS</sub> = 0V	±10			V
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±8V, V <sub>DS</sub> = 0V		±0.01	±50	nA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = 5V, I <sub>D</sub> = 100 μA	0.3		1.5	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 5V, V <sub>GS</sub> = 0V			1	μA
Forward Transfer Admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 5V, I <sub>D</sub> = 50mA, f = 1kHz		80		mS
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 5V, V <sub>GS</sub> = 0V, f = 1MHz		50		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 5V, V <sub>GS</sub> = 0V, f = 1MHz		10		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	V <sub>DS</sub> = 5V, V <sub>GS</sub> = 0V, f = 1MHz		5		pF
Static Drain-to-Source on state Resistance	R <sub>DS(on)1</sub>	V <sub>GS</sub> = 5V, I <sub>D</sub> = 50mA		5	7	Ω
	R <sub>DS(on)2</sub>	V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 15mA		7	12	Ω

Marking : NJ

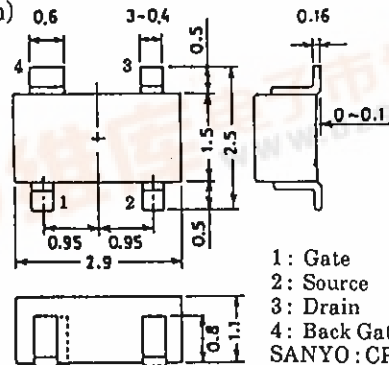
**Electrical Connection**



A01526

**Package Dimensions 2100A**

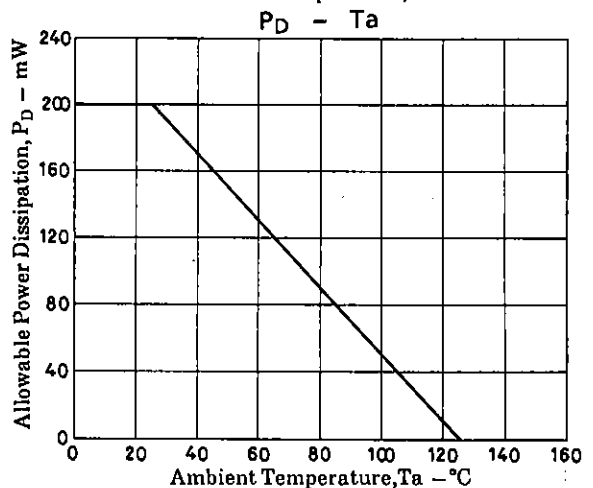
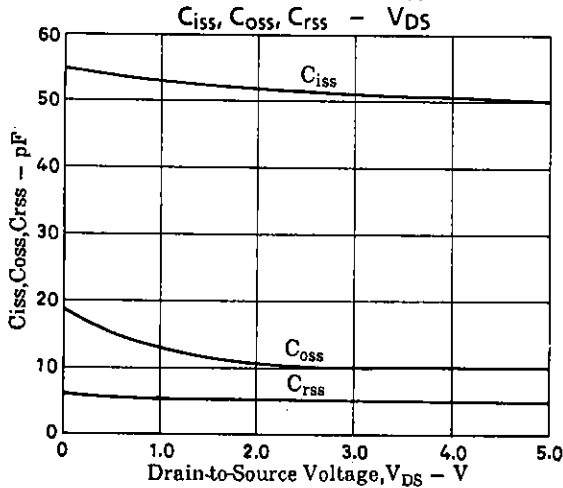
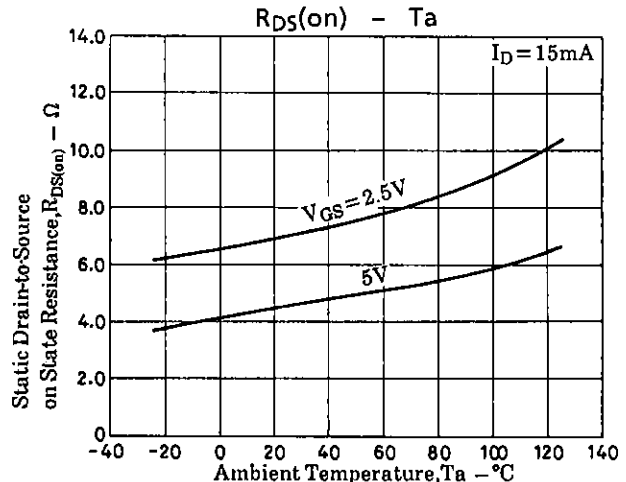
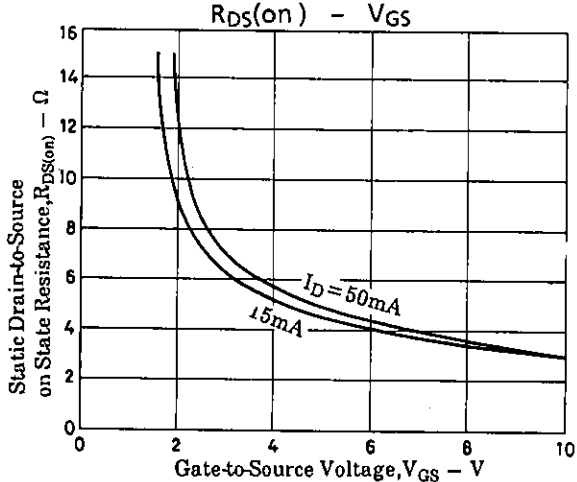
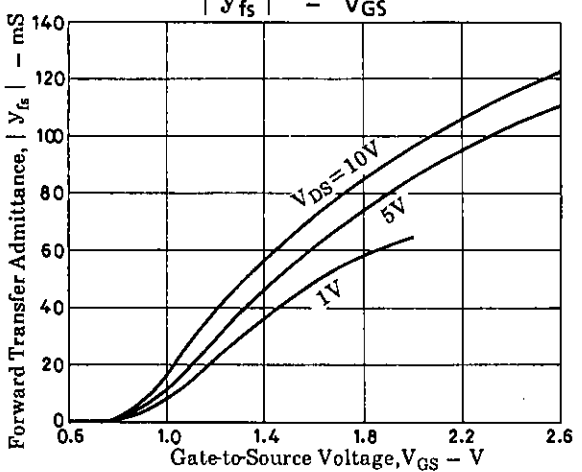
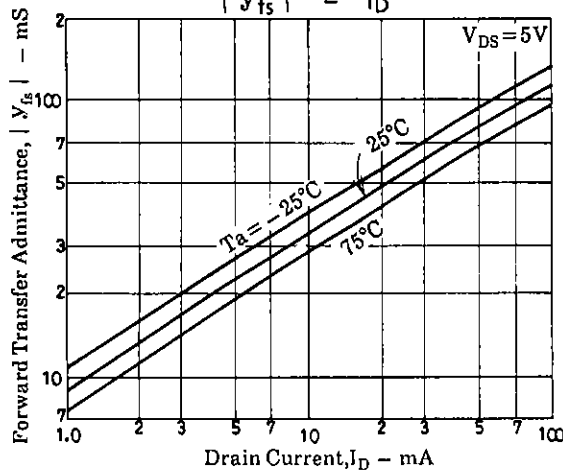
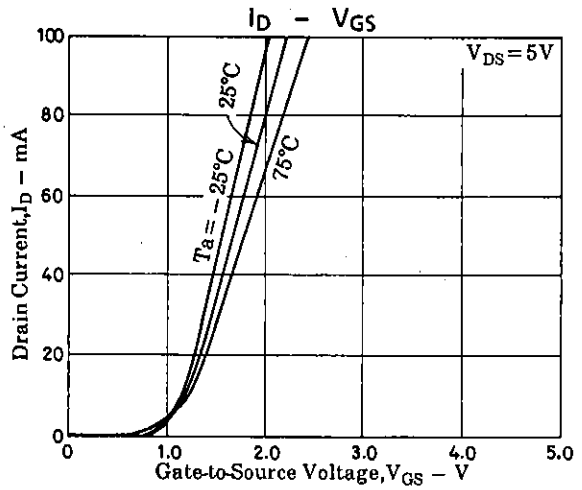
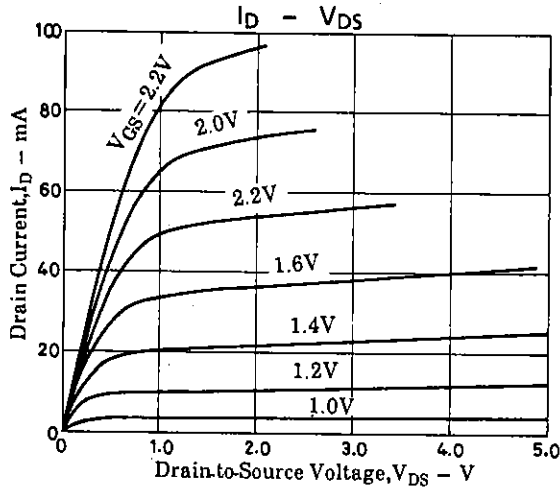
(unit : mm)



1: Gate  
2: Source  
3: Drain  
4: Back Gate  
SANYO: CP4



3SK248



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